

## isc Silicon NPN Darlington Power Transistor

2SD2022

## DESCRIPTION

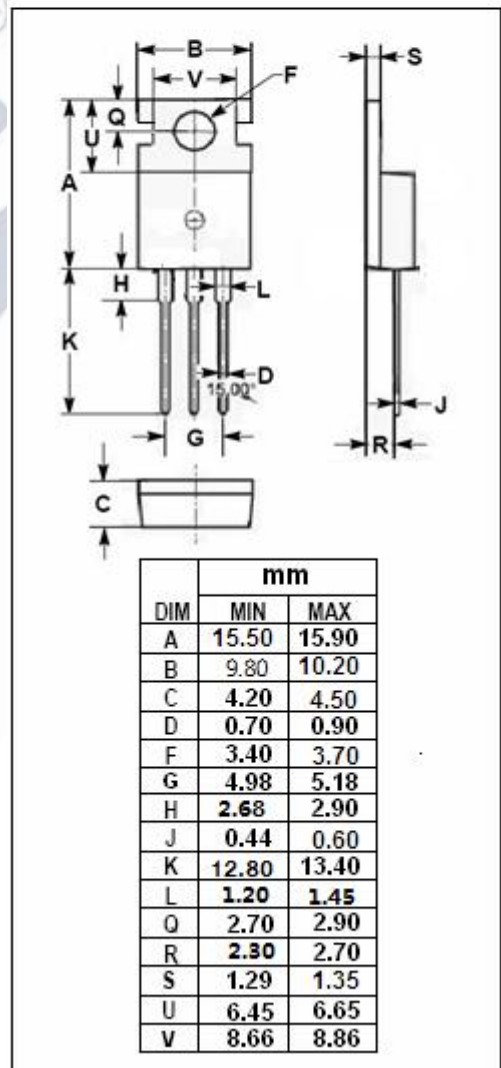
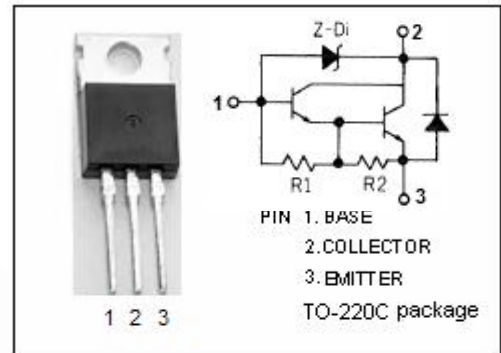
- High DC Current Gain-  
:  $h_{FE} = 3000(\text{Min}) @ I_C = 1\text{A}$
- Low Collector-Emitter Saturation Voltage-  
:  $V_{CE(\text{sat})} = 1.5\text{V}(\text{Max}) @ I_C = 1\text{A}$
- Incorporating a built-in zener diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Low-frequency amplifications.
- Power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	50-70	V
$V_{CEO}$	Collector-Emitter Voltage	50-70	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	2	A
$I_{CM}$	Base Current-Peak	3	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Darlington Power Transistor****2SD2022****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	50		70	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =0.1mA; I <sub>E</sub> = 0	50		70	V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 3mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 1mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 1mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	3000			